

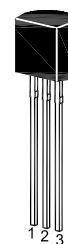
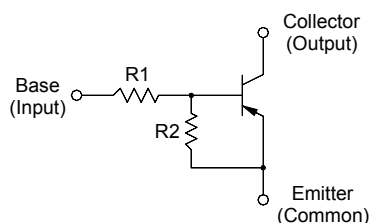
# RA101S...RA106S

## PNP Silicon Epitaxial Planar Transistor

for switching and interface circuit and drive circuit applications

### Features

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process



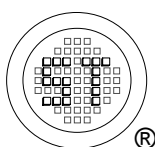
1. Emitter 2. Collector 3. Base  
TO-92 Plastic Package

### Resistor Values

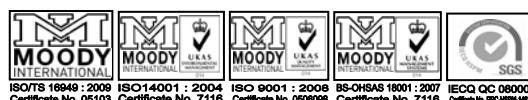
Type	R1 (K $\Omega$ )	R2 (K $\Omega$ )
RA101S	4.7	4.7
RA102S	10	10
RA103S	22	22
RA104S	47	47
RA105S	2.2	47
RA106S	4.7	47

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter		Symbol	Value	Unit
Output Voltage		$-V_o$	50	V
Input Voltage	RA101S	$-V_i$	20, -10	V
	RA102S		30, -10	
	RA103S		40, -10	
	RA104S		40, -10	
	RA105S		12, -5	
	RA106S		20, -5	
Output Current		$-I_o$	100	mA
Total Power Dissipation		$P_{tot}$	200	mW
Junction Temperature		$T_j$	150	$^\circ\text{C}$
Storage Temperature Range		$T_{stg}$	- 55 to + 150	$^\circ\text{C}$



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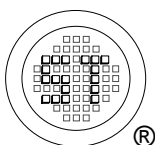


# RA101S...RA106S

## Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $-V_o = 5\text{ V}$ , $-I_o = 10\text{ mA}$	RA101S RA102S RA103S RA104S RA105S RA106S $G_I$	30 50 70 80 80 80	- - - - - -	- - - - - -	- - - - - -
Output Cutoff Current at $-V_o = 50\text{ V}$	$-I_{O(OFF)}$	-	-	500	nA
Input Current at $-V_i = 5\text{ V}$	RA101S RA102S RA103S RA104S RA105S RA106S $-I_i$	- - - - - -	- - - - - -	1.8 0.88 0.36 0.18 3.6 1.8	mA
Output Voltage at $-I_o = 10\text{ mA}$ , $-I_i = 0.5\text{ mA}$	$-V_{O(ON)}$	-	-	0.3	V
Input Voltage (ON) at $-V_o = 0.2\text{ V}$ , $-I_o = 5\text{ mA}$	RA101S RA102S RA103S RA104S RA105S RA106S $-V_{I(ON)}$	- - - - - -	- - - - - -	2 2.4 3 5 1.1 1.3	V
Input Voltage (OFF) at $-V_o = 5\text{ V}$ , $-I_o = 0.1\text{ mA}$	RA101S~104S RA105S~106S $-V_{I(OFF)}$	1 0.5	- -	- -	V
Transition Frequency at $-V_o = 10\text{ V}$ , $-I_o = 5\text{ mA}$	$f_T$ <sup>1)</sup>	-	200	-	MHz

<sup>1)</sup> Characteristic of transistor only.

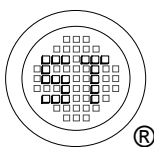
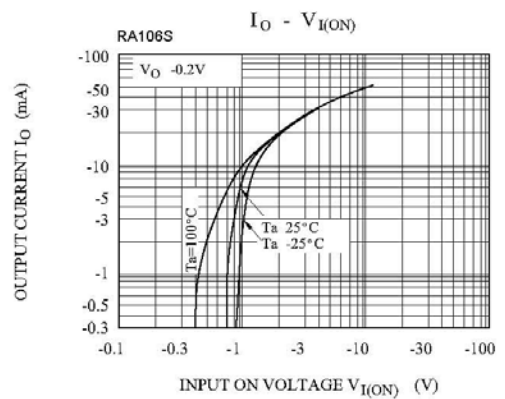
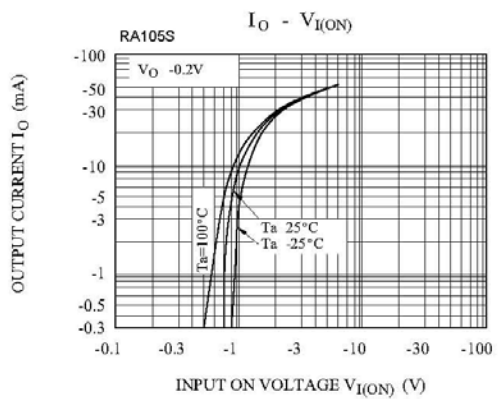
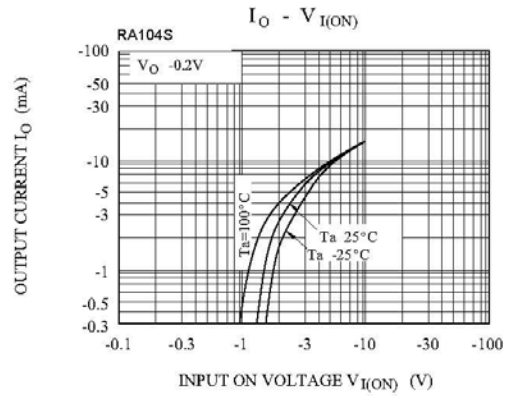
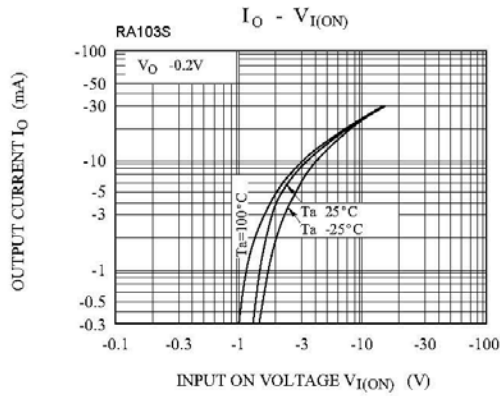
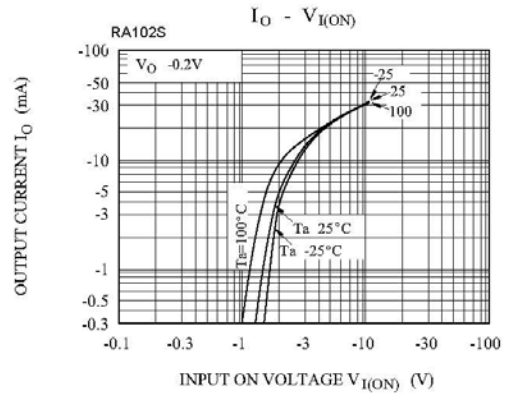
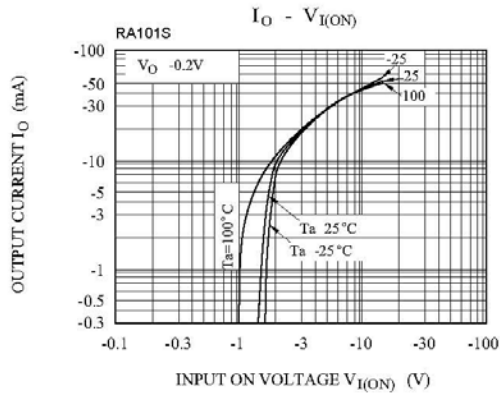


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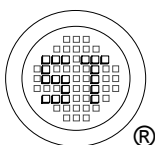
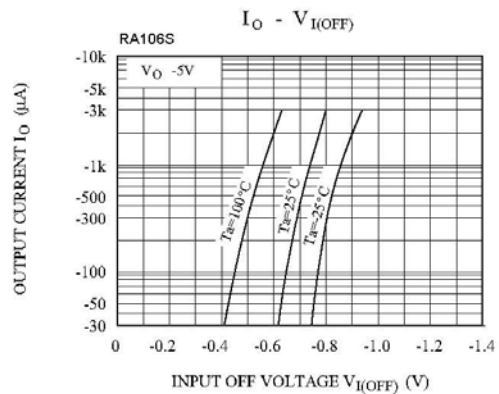
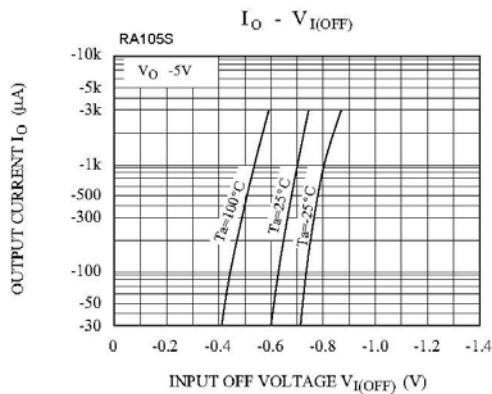
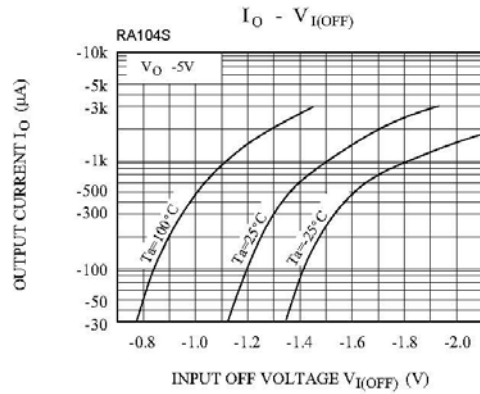
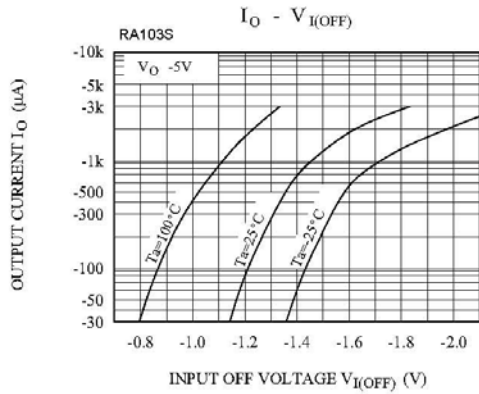
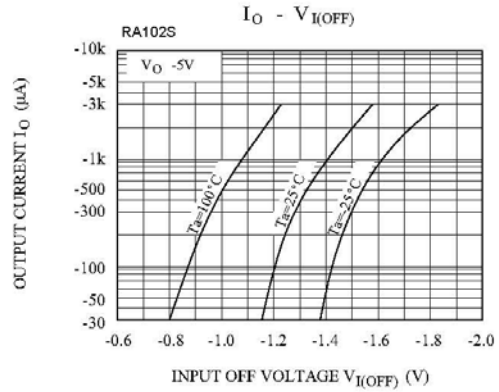
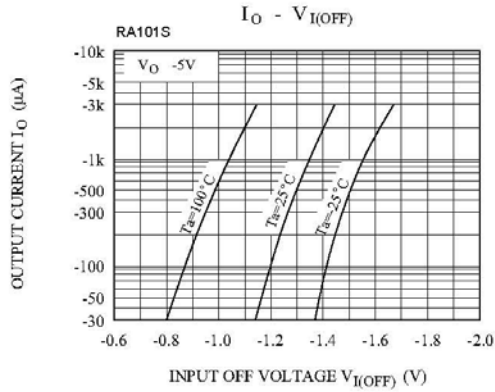
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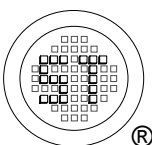
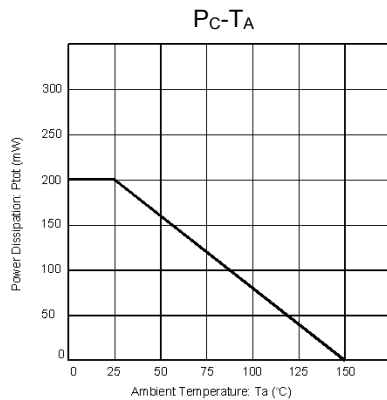
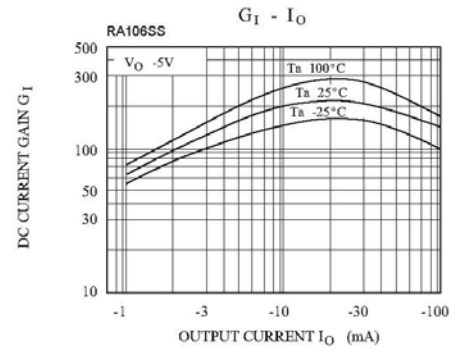
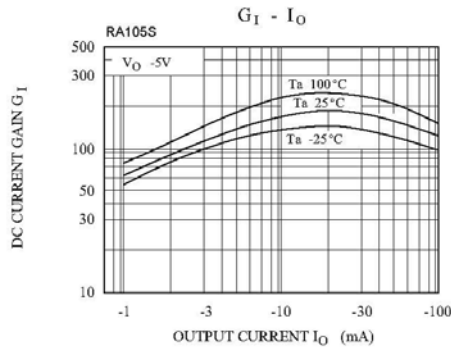
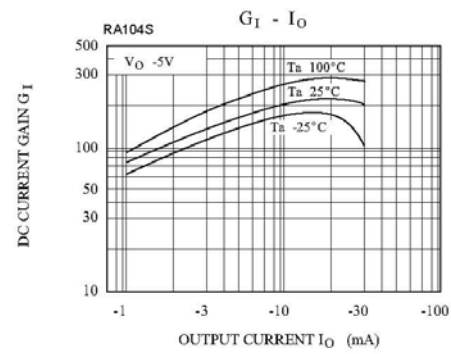
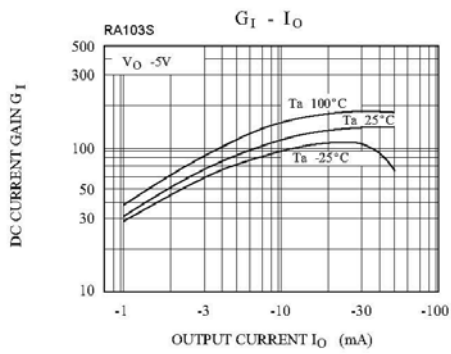
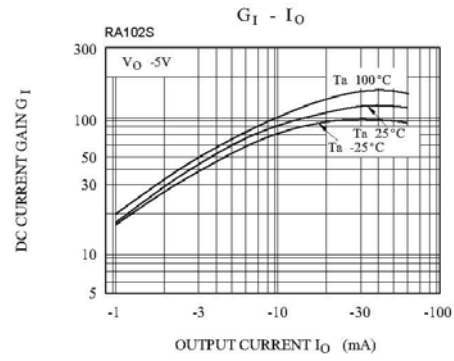
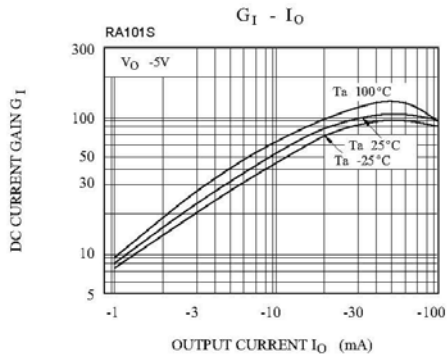
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